IN THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

Claims 1 – 11 (Cancelled)

12. (New) A member for a semiconductor device comprising a base member made of an alloy or composite mainly composed of Cu and W and/or Mo, wherein a coating layer made of a hard carbon film is provided on at least a surface of the base member on which another member for the semiconductor device is bonded with a resin.

13. (New) The member for a semiconductor device according to claim 12, wherein the alloy or composite mainly composed of Cu and W and/or Mo contains Cu of 5 to 40% by weight.

14. (New) A member for a semiconductor device comprising a base member made of an alloy or composite mainly composed of Al-SiC, wherein a coating layer made of a hard carbon film is provided on at least a surface of the base member on which another member for the semiconductor device is bonded with a resin.

15. (New) The member for a semiconductor device according to claim 14, wherein the alloy or composite mainly composed of Al-SiC contains SiC of 10 to 70% by weight.

16. (New) A member for a semiconductor device comprising a base member made of an alloy or composite mainly composed of Si-SiC, wherein a coating layer made of a hard carbon film is provided on at least a surface of the base member on which another member for the semiconductor device is bonded with a resin.

17. (New) The member for a semiconductor device according to claim 16, wherein the alloy or composite mainly composed of Si-SiC contains Si of 10 to 35% by weight.

18. (New) The member for a semiconductor device according to claim 12, wherein the coating layer has a thickness of 0.1 to 10 μm.

19. (New) The member for a semiconductor device according to claim 14, wherein the coating layer has a thickness of 0.1 to 10 μm.

20. (New) The member for a semiconductor device according to claim 16, wherein the coating layer has a thickness of 0.1 to 10 μm.

21. (New) The member for a semiconductor device according to claim 12, wherein the surface of the base member on which the coating layer is formed has a surface roughness of 0.1 to 20 μm in Rmax.

22. (New) The member for a semiconductor device according to claim 14, wherein the surface of the base member on which the coating layer is formed has a surface roughness of 0.1 to 20 μm in Rmax.

23. (New) The member for a semiconductor device according to claim 16, wherein the surface of the base member on which the coating layer is formed has a surface roughness of 0.1 to 20 μm in Rmax.

24. (New) The member for a semiconductor device according to claim 12, wherein pores in the surface of the base member on which the coating layer is formed have a depth of 100 μm or less.

25. (New) The member for a semiconductor device according to claim 14, wherein pores in the surface of the base member on which the coating layer is formed have a depth of 100 μm or less.

26. (New) The member for a semiconductor device according to claim 16, wherein pores in the surface of the base member on which the coating layer is formed have a depth of 100 μm or less.

27. (New) The member for a semiconductor device according to claim 12, wherein a plating layer of Ni is provided between the coating layer and the surface of the base member on which the coating layer is formed.

28. (New) The member for a semiconductor device according to claim 14, wherein a plating layer of Ni is provided between the coating layer and the surface of the base member on which the coating layer is formed.

29. (New) The member for a semiconductor device according to claim 16, wherein a plating layer of Ni is provided between the coating layer and the surface of the base member on which the coating layer is formed.

30. (New) A semiconductor device employing the member for a semiconductor device according to claim 12.

31. (New) A semiconductor device employing the member for a semiconductor device according to claim 14.

32. (New) A semiconductor device employing the member for a semiconductor device according to claim 16.